

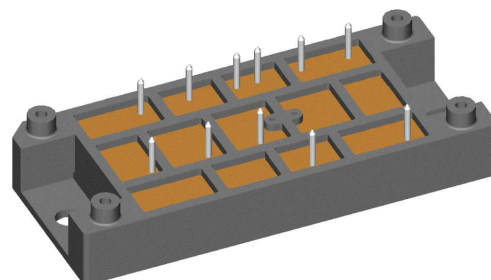
Thyristor Module

3~ Rectifier	Brake Chopper
$V_{RRM} = 1600 \text{ V}$	$V_{CES} = 1200 \text{ V}$
$I_{DAV} = 180 \text{ A}$	$I_{C25} = 180 \text{ A}$
$I_{FSM} = 700 \text{ A}$	$V_{CE(sat)} = 1.7 \text{ V}$

3~ Rectifier Bridge, half-controlled (high-side) + Brake Unit

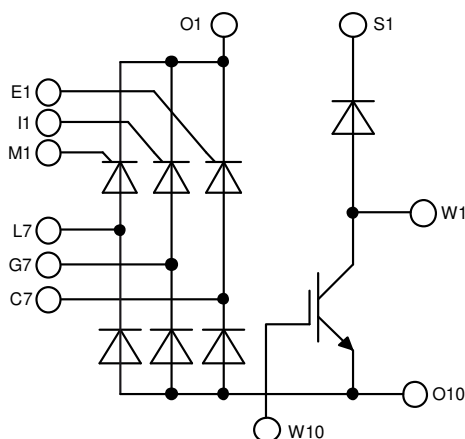
Part number

VVZB120-16ioX



Backside: isolated

 E72873



Features / Advantages:

- Package with DCB ceramic base plate
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current
- X2PT - 2nd generation Xtreme light Punch Through
- Rugged X2PT design results in:
 - short circuit rated for 10 μsec .
 - very low gate charge
 - low EMI
 - square RBSOA @ 2x I_c
- Thin wafer technology combined with X2PT design results in a competitive low $V_{CE(sat)}$ and low thermal resistance

Applications:

- 3~ Rectifier with brake unit for drive inverters

Package: V2-Pack

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Height: 17 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

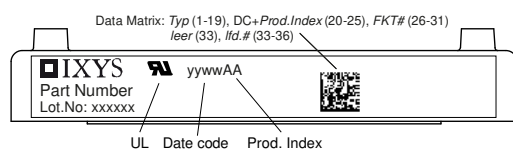
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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1700	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				1600	V
$I_{R/D}$	reverse current, drain current	$V_{R/D} = 1600\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			50	μA
		$V_{R/D} = 1600\text{ V}$	$T_{VJ} = 150^{\circ}\text{C}$			20	mA
V_T	forward voltage drop	$I_T = 60\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1.27	V
		$I_T = 180\text{ A}$				1.90	V
		$I_T = 60\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			1.25	V
		$I_T = 180\text{ A}$				2.04	V
I_{DAV}	bridge output current	$T_C = 85^{\circ}\text{C}$ rectangular $d = \frac{1}{3}$	$T_{VJ} = 150^{\circ}\text{C}$			180	A
V_{T0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}\text{C}$			0.83	V
r_T	slope resistance					6.9	m Ω
R_{thJC}	thermal resistance junction to case					0.5	K/W
R_{thCH}	thermal resistance case to heatsink				0.1		K/W
P_{tot}	total power dissipation		$T_C = 25^{\circ}\text{C}$			250	W
I_{TSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			700	A
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			755	A
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			595	A
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			645	A
I^2t	value for fusing	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}\text{C}$			2.45	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			2.37	kA ² s
		$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}\text{C}$			1.77	kA ² s
		$t = 8,3\text{ ms}; (60\text{ Hz}), \text{ sine}$	$V_R = 0\text{ V}$			1.73	kA ² s
C_J	junction capacitance	$V_R = 400\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}\text{C}$		54		pF
P_{GM}	max. gate power dissipation	$t_p = 30\text{ }\mu\text{s}$	$T_C = 150^{\circ}\text{C}$			10	W
		$t_p = 300\text{ }\mu\text{s}$				5	W
P_{GAV}	average gate power dissipation					0.5	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 150^{\circ}\text{C}; f = 50\text{ Hz}$ repetitive, $I_T = 180\text{ A}$				150	A/ μs
		$t_p = 200\text{ }\mu\text{s}; di_G/dt = 0.45\text{ A}/\mu\text{s};$ $I_G = 0.45\text{ A}; V = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 60\text{ A}$				500	A/ μs
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$ $R_{GK} = \infty$; method 1 (linear voltage rise)	$T_{VJ} = 150^{\circ}\text{C}$			1000	V/ μs
V_{GT}	gate trigger voltage	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			1.5	V
			$T_{VJ} = -40^{\circ}\text{C}$			1.6	V
I_{GT}	gate trigger current	$V_D = 6\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			95	mA
			$T_{VJ} = -40^{\circ}\text{C}$			200	mA
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 150^{\circ}\text{C}$			0.2	V
I_{GD}	gate non-trigger current					10	mA
I_L	latching current	$t_p = 10\text{ }\mu\text{s}$	$T_{VJ} = 25^{\circ}\text{C}$			450	mA
		$I_G = 0.45\text{ A}; di_G/dt = 0.45\text{ A}/\mu\text{s}$					
I_H	holding current	$V_D = 6\text{ V}$ $R_{GK} = \infty$	$T_{VJ} = 25^{\circ}\text{C}$			200	mA
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}\text{C}$			2	μs
		$I_G = 0.45\text{ A}; di_G/dt = 0.45\text{ A}/\mu\text{s}$					
t_q	turn-off time	$V_R = 100\text{ V}; I_T = 60\text{ A}; V = \frac{2}{3} V_{DRM}$ $di/dt = 10\text{ A}/\mu\text{s}$ $dv/dt = 20\text{ V}/\mu\text{s}$ $t_p = 200\text{ }\mu\text{s}$	$T_{VJ} = 125^{\circ}\text{C}$		150		μs

Brake IGBT + Diode				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{CES}	collector emitter voltage	$T_{VJ} = 25^{\circ}\text{C}$				1200	V
V_{GES}	max. DC gate voltage					± 20	V
V_{GEM}	max. transient gate emitter voltage					± 30	V
I_{C25}	collector current	$T_C = 25^{\circ}\text{C}$				180	A
I_{C80}		$T_C = 80^{\circ}\text{C}$				140	A
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				500	W
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 100\text{ A}; V_{GE} = 15\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$		1.7	2.1	V
			$T_{VJ} = 125^{\circ}\text{C}$		1.9		V
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 4\text{ mA}; V_{GE} = V_{CE}$	$T_{VJ} = 25^{\circ}\text{C}$	6	6.8	7.5	V
I_{CES}	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			0.1	mA
			$T_{VJ} = 125^{\circ}\text{C}$		0.1		mA
I_{GES}	gate emitter leakage current	$V_{GE} = \pm 20\text{ V}$				500	nA
$Q_{G(on)}$	total gate charge	$V_{CE} = 600\text{ V}; V_{GE} = 15\text{ V}; I_C = 100\text{ A}$			340		nC
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 600\text{ V}; I_C = 100\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 6.8\ \Omega$	$T_{VJ} = 125^{\circ}\text{C}$		230		ns
t_r	current rise time				70		ns
$t_{d(off)}$	turn-off delay time				380		ns
t_f	current fall time				230		ns
E_{on}	turn-on energy per pulse				12.5		mJ
E_{off}	turn-off energy per pulse				11.5		mJ
RBSOA	reverse bias safe operating area	$V_{GE} = \pm 15\text{ V}; R_G = 6.8\ \Omega$	$T_{VJ} = 125^{\circ}\text{C}$				
I_{CM}		$V_{CEK} = 1200\text{ V}$				300	A
SCSOA	short circuit safe operating area	$V_{CEK} = 1200\text{ V}$					
t_{SC}	short circuit duration	$V_{CE} = 720\text{ V}; V_{GE} = \pm 15$	$T_{VJ} = 125^{\circ}\text{C}$			10	μs
I_{SC}	short circuit current	$R_G = 6.8\ \Omega$; non-repetitive			450		A
R_{thJC}	thermal resistance junction to case					0.25	K/W
R_{thCH}	thermal resistance case to heatsink				0.10		K/W
Brake Diode							
V_{RRM}	max. repetitive reverse voltage		$T_{VJ} = 25^{\circ}\text{C}$			1200	V
I_{F25}	forward current		$T_C = 25^{\circ}\text{C}$			48	A
I_{F80}			$T_C = 80^{\circ}\text{C}$			32	A
V_F	forward voltage	$I_F = 30\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			2.75	V
			$T_{VJ} = 125^{\circ}\text{C}$		1.60		V
I_R	reverse current	$V_R = V_{RRM}$	$T_{VJ} = 25^{\circ}\text{C}$			0.25	mA
			$T_{VJ} = 125^{\circ}\text{C}$			1	mA
Q_{rr}	reverse recovery charge	$V_R = 600\text{ V}$ $-di_F/dt = 1000\text{ A}/\mu\text{s}$ $I_F = 30\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 125^{\circ}\text{C}$		5.2		μC
I_{RM}	max. reverse recovery current				50		A
t_{rr}	reverse recovery time				300		ns
E_{rec}	reverse recovery energy				1.9		mJ
R_{thJC}	thermal resistance junction to case					0.9	K/W
R_{thCH}	thermal resistance case to heatsink				0.3		K/W

Package V2-Pack			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			100	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		125	°C
Weight				76		g
M_D	mounting torque		2		2.5	Nm
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal	6.0			mm
$d_{Spb/Apb}$		terminal to backside	12.0			mm
V_{ISOL}	isolation voltage	t = 1 second	3600			V
		t = 1 minute	3000			V

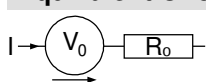


Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VVZB120-16ioX	VVZB120-16ioX	Box	6	511152

Equivalent Circuits for Simulation

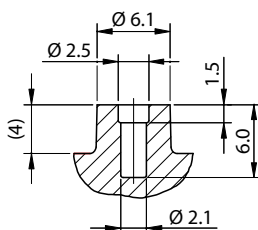
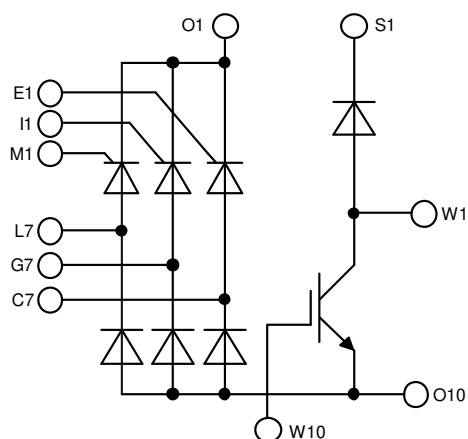
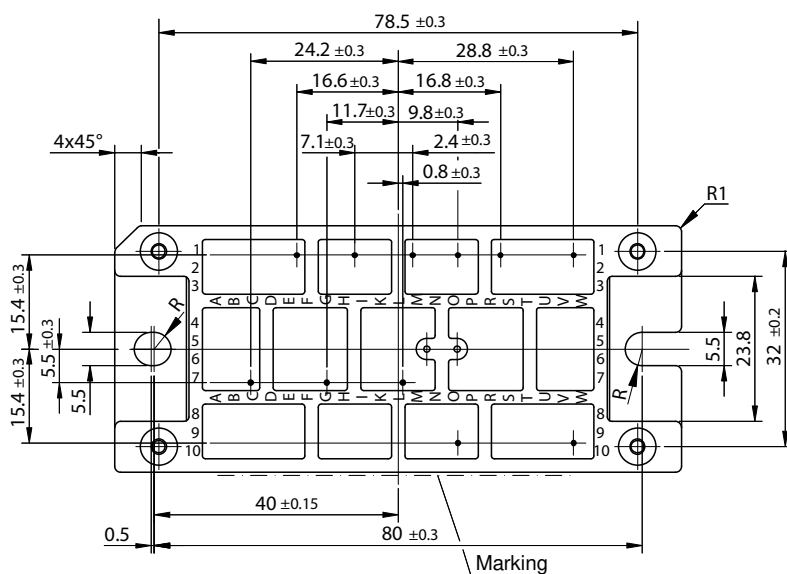
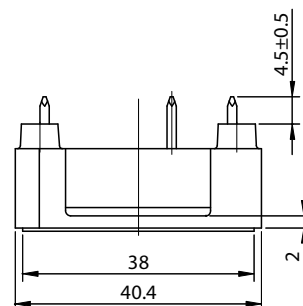
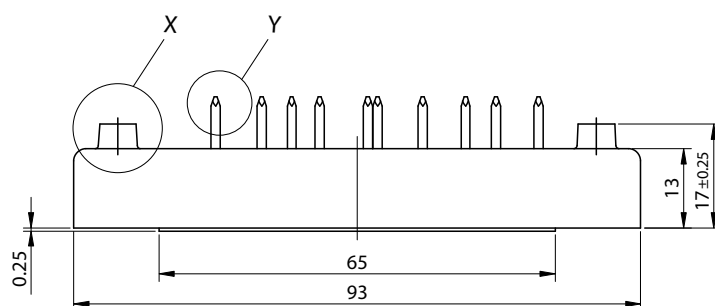
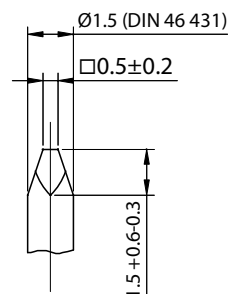
* on die level

$T_{VJ} = 150^{\circ}\text{C}$

		Thyristor	Brake Diode	
$V_{0\max}$	threshold voltage	0.83	1.31	V
$R_{0\max}$	slope resistance *	3.7	8	mΩ

Outlines V2-Pack
Remarks:

EJOT PT® self-tapping screws of the dimension K25 are recommended for the mechanical connection between module and PCB. Choose the right length according to your board thickness at a maximum depth of 6 mm of the module holes.¹ The recommended mounting torque is 1.5 Nm.

Detail X M 2:1

Detail Y M 5:1


Thyristor

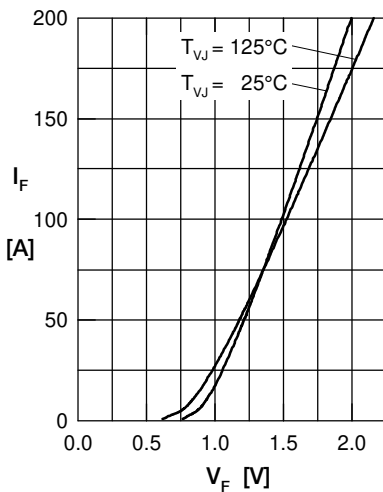


Fig. 1 Forward current vs. voltage drop per thyristor

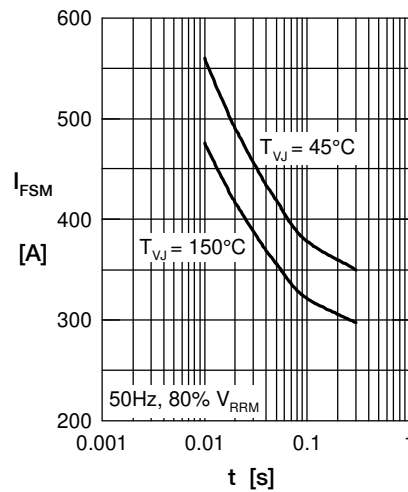


Fig. 2 Surge overload current vs. time per thyristor

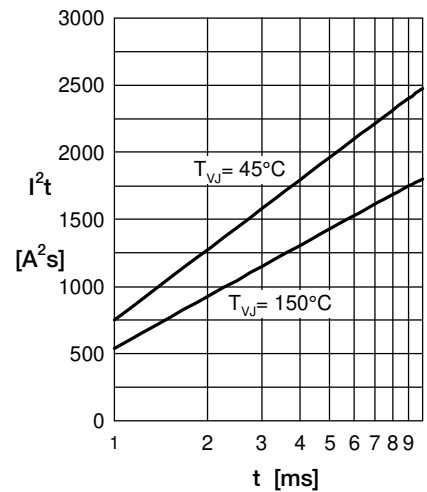


Fig. 3 I^2t vs. time per thyristor

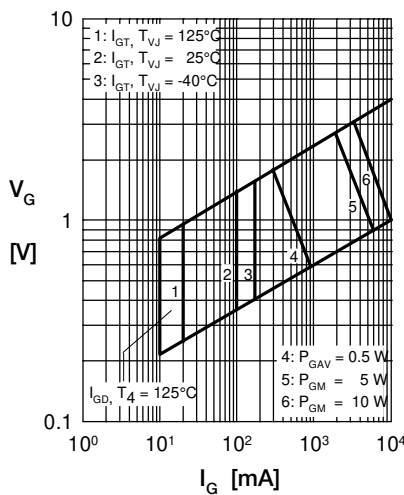


Fig. 4 Gate trigger characteristics

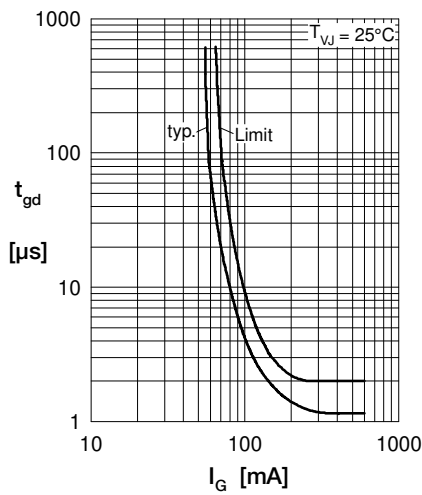


Fig. 5 Gate trigger delay time

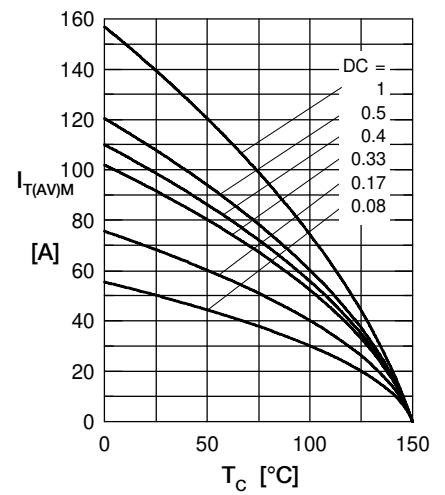


Fig. 5 Max. forward current vs. case temperature per thyristor

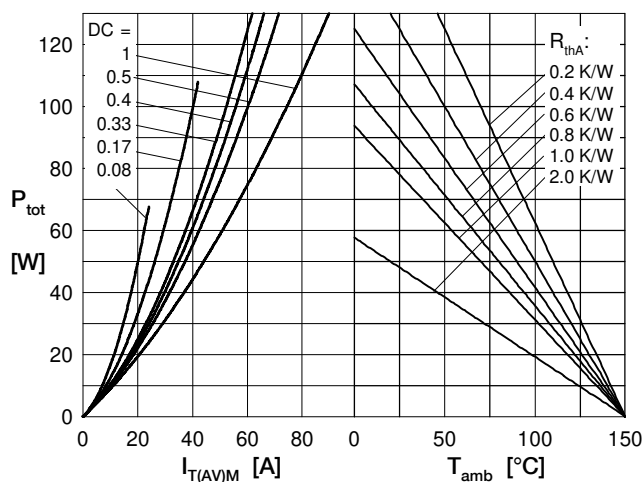


Fig. 4 Power dissipation vs. forward current and ambient temperature per thyristor

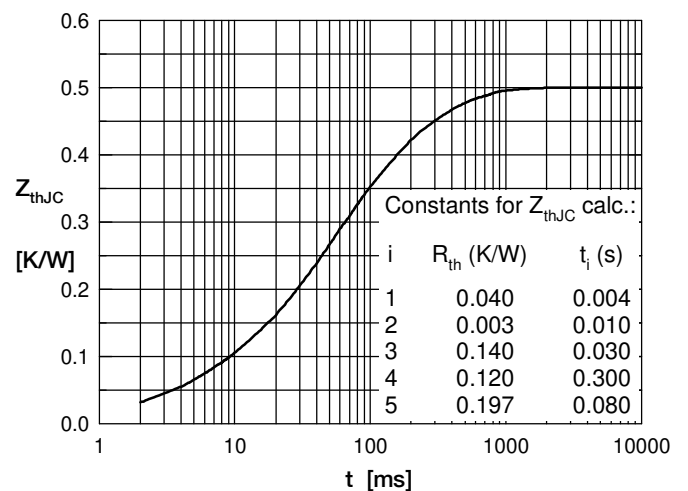


Fig. 6 Transient thermal impedance junction to case vs. time per thyristor

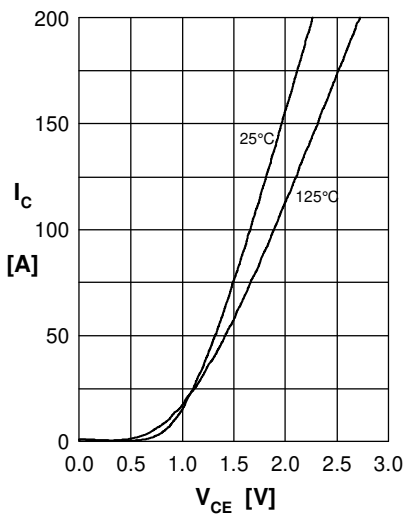
Brake IGBT + Diode


Fig.1 Output characteristics IGBT

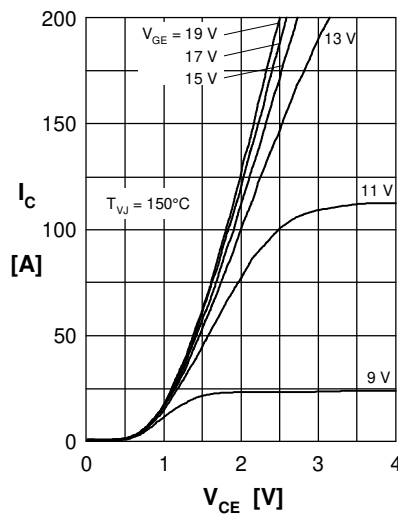


Fig.2 Typ. output characteristics IGBT

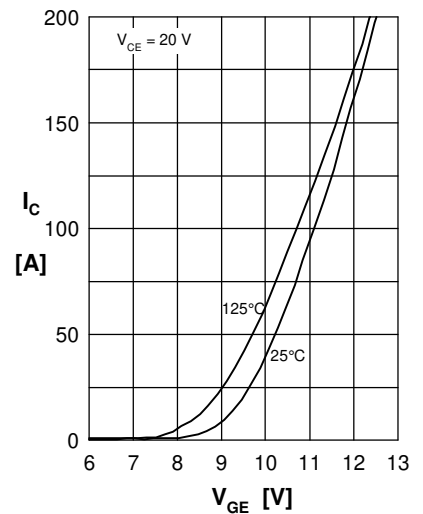


Fig.3 Typ. transfer charact. IGBT

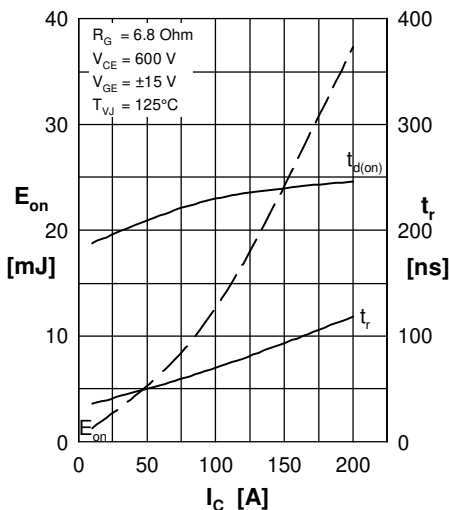


Fig.4 Typ. turn-on energy & switch. times vs. collector current

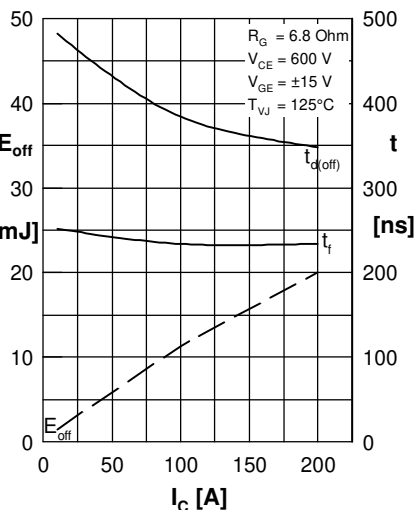


Fig.5 Typ. turn-off energy & switch. times vs. collector current

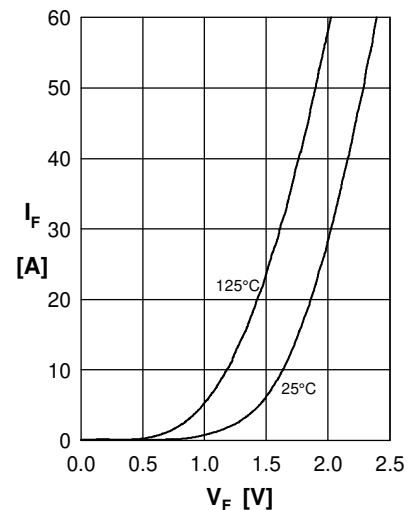


Fig.6 Typ. forward characteristics Diode

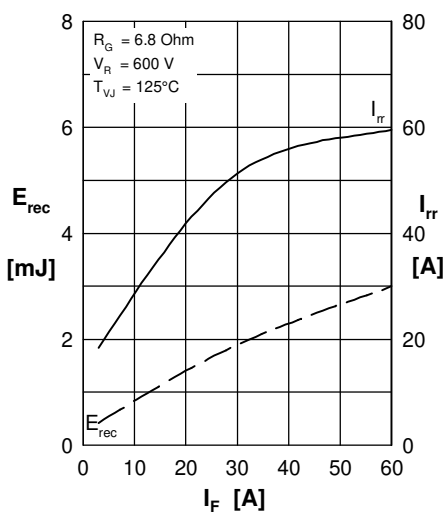


Fig.7 Typ. reverse recovery characteristics Diode

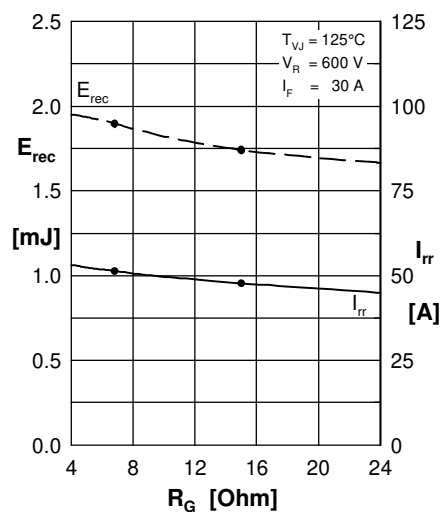


Fig.8 Typ. reverse recovery characteristics Diode

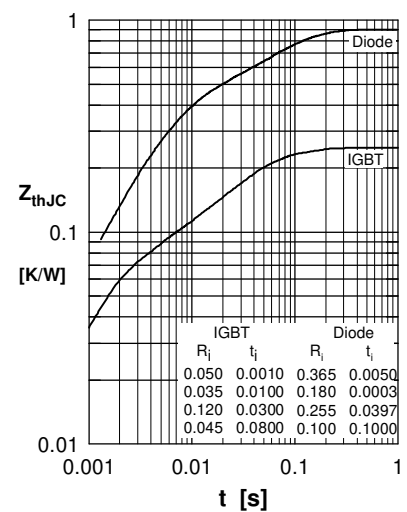


Fig.9 Transient thermal resistance junction to case